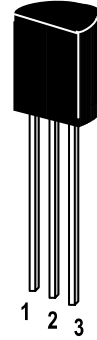


ST 2SA1585

PNP Silicon Epitaxial Planar Transistor

The transistor is subdivided into two groups, Q and R, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

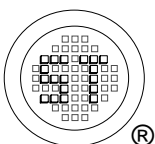
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	20	V
Collector Emitter Voltage	$-V_{CEO}$	20	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_{C(1)}$ $-I_{CP}$	2 5	A
Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$

¹⁾ Single pulse $P_w = 10$ ms

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 2$ V, $-I_C = 100$ mA Current Gain Group	Q h_{FE}	120	-	270	-
	R h_{FE}	180	-	390	-
Collector Base Breakdown Voltage at $-I_C = 50$ μA	$-V_{(BR)CBO}$	20	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1$ mA	$-V_{(BR)CEO}$	20	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 50$ μA	$-V_{(BR)EBO}$	6	-	-	V
Collector Cutoff Current at $-V_{CB} = 20$ V	$-I_{CBO}$	-	-	100	nA
Emitter Cutoff Current at $-V_{EB} = 5$ V	$-I_{EBO}$	-	-	100	nA
Collector Emitter Saturation Voltage at $-I_C = 2$ A, $-I_B = 0.1$ A	$-V_{CE(sat)}$	-	-	0.5	V
Transition Frequency at $-V_{CE} = 2$ V, $I_E = 500$ mA, $f = 100$ MHz	f_T	-	240	-	MHz
Output Capacitance at $-V_{CB} = 10$ V, $f = 1$ MHz	C_{OB}	-	35	-	pF



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Certificate No. 7116

ISO 9001:2000
Certificate No. 0506098

Dated : 28/07/2006

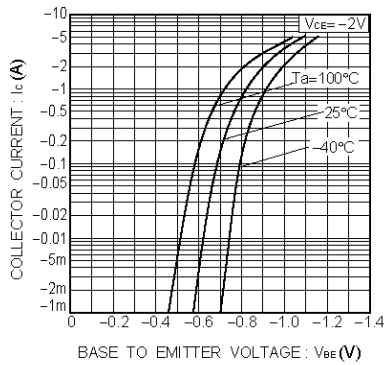


Fig.1 Grounded emitter propagation characteristics

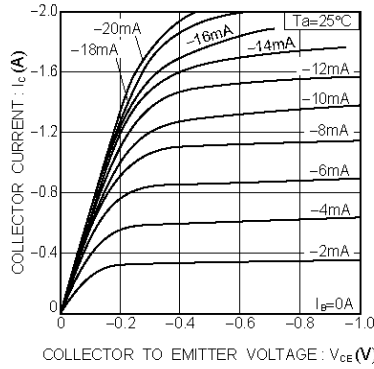


Fig.2 Grounded emitter output characteristics (I)

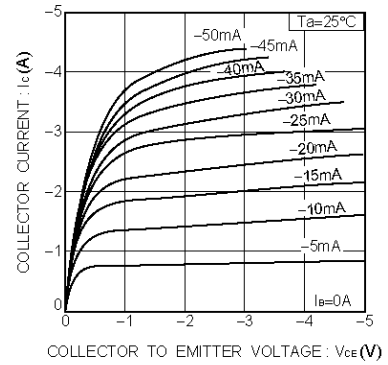


Fig.3 Grounded emitter output characteristics (II)

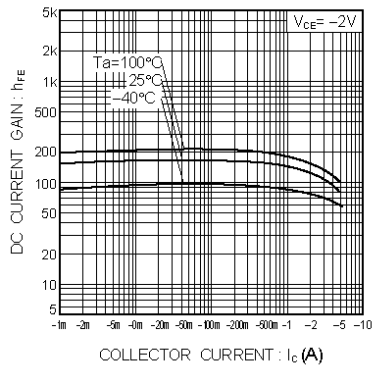


Fig.4 DC current gain vs. collector current

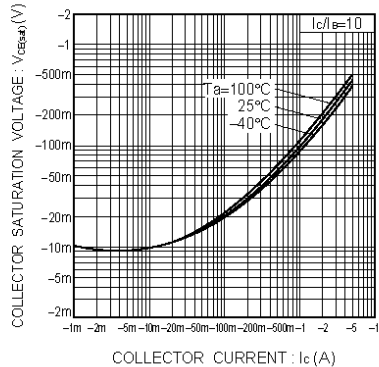


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

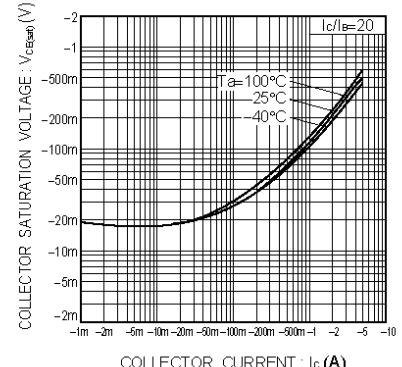


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

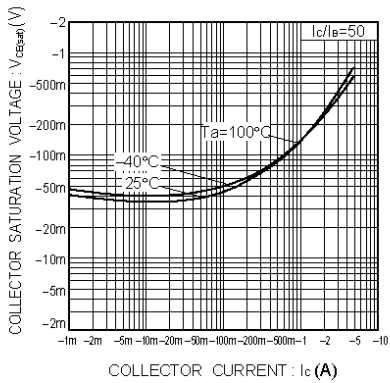


Fig.7 Collector-emitter saturation voltage vs. collector current (III)

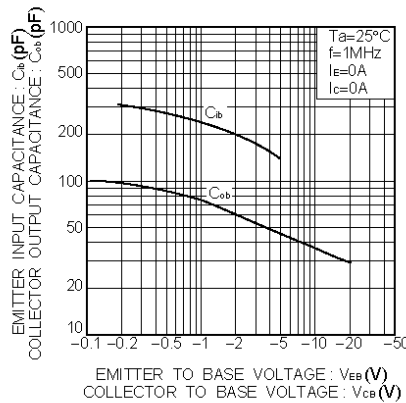


Fig.8 Gain bandwidth product vs. emitter current
Collector output capacitance vs. collector-base voltage

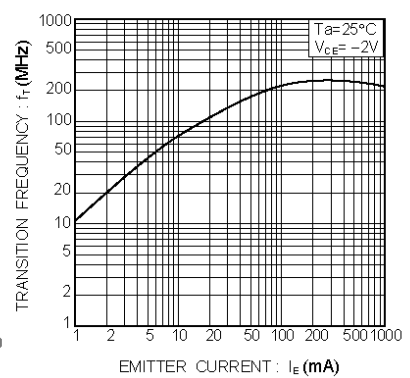
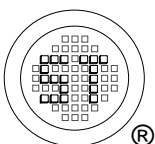


Fig.9 Emitter input capacitance vs. emitter base voltage



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